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Maximum Power Dissipation Rating:

1.5 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Milstar

Features Provided:

Burn in, mil-std-883, class b and electrostatic sensitive and radiation hardened and selected item and tested to mil-std-883 and w/reset and

frequency compensated

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Input Circuit Pattern:

32 input

Criticality Code Justification:

Cbbl

Current Rating Per Characteristic:

-10.00 milliamperes collector cutoff current, dc, with specified resistance between base and emitter microamperes and 10.00 milliamperes

reverse current, dc microamperes

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, digital, microcontroller

Voltage Rating And Type Per Characteristic:

4.0 volts power source and 6.0 volts power source and -0.5 volts input and 6.5 volts input

Memory Device Type:

Ram

Special Features:

Device is a cmos, 8-bit microcontroller with 256 x 8 ram; this is a selected item made from rc351-3816-012 which is made from

351-3816-012 which is a 1ch66 80c32/bqa (signetics); case outline designator gdip1-t40 or cdip2-t40 as designated in mil-std-1835; oscillator

frequency is from 3.5 to 12.0 mhz

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

40 printed circuit

Shelf Life:

N/a

Unit Of Measure:

Domilitorization

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